

Deposition of Alkanethiolate Self-Assembled Monolayers on Germanium

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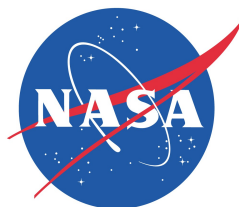
Department of Chemistry and Biochemistry²

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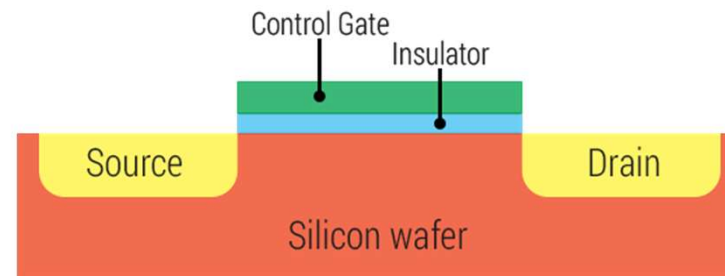


Motivation and Background

- Problem: Ge form unstable oxides that inhibit device performance.
 - Need to find effective surface passivation method for Ge at reasonable time scales
 - Passivation layer = coat of protective material that reduces the amount of chemical reactivity on the surface

Material	Hole Mobility (cm ² V/s)
Silicon	200
Germanium	450

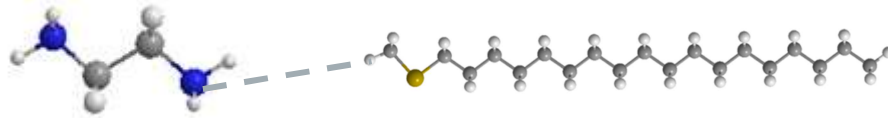
Del Alamo, Jesús A. "Nanometre-scale electronics with III-V compound semiconductors." *Nature* 479.7373 (2011): 317-323.



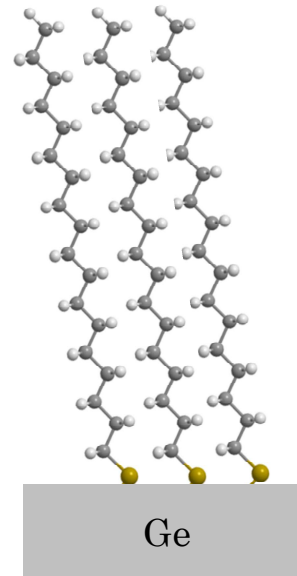
https://www.androidcentral.com/sites/androidcentral.com/files/styles/xlarge/public/article_images/2015/01/Transistor.png

Motivation and Background

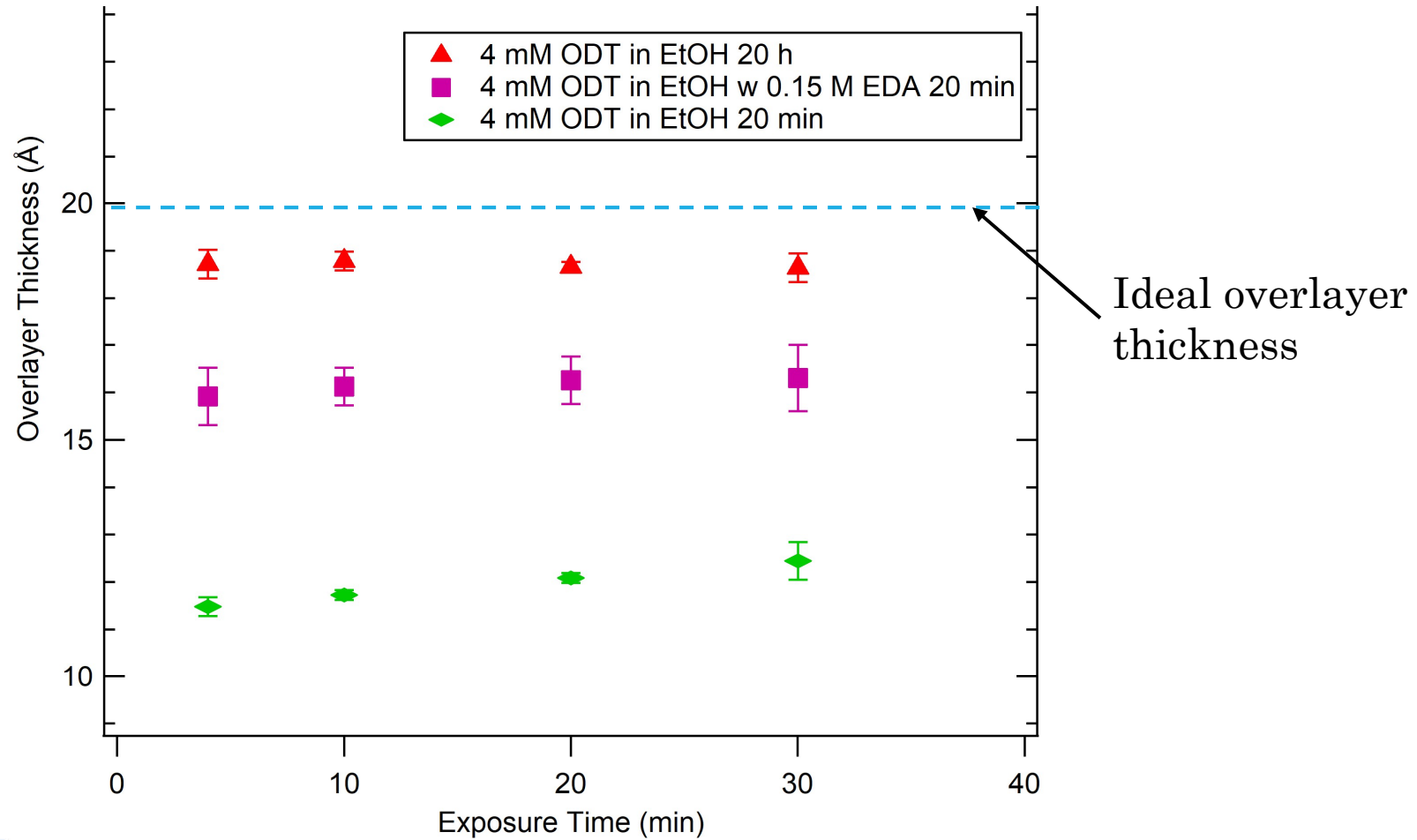
- Use octadecanethiol (ODT) as passivation reagent.
 - Long-chain thiol
 - Used successfully in literature, but at long time scales (20 h)
 - Not practical for industry
- **Goal:** reduce passivation time by adding ethylenediamine (EDA)



EDA converts thiol to thiolate.

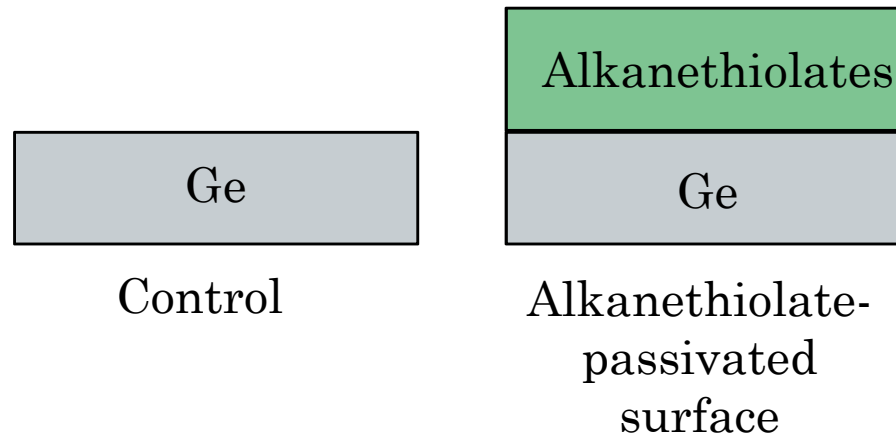


Adding amine increases layer thickness

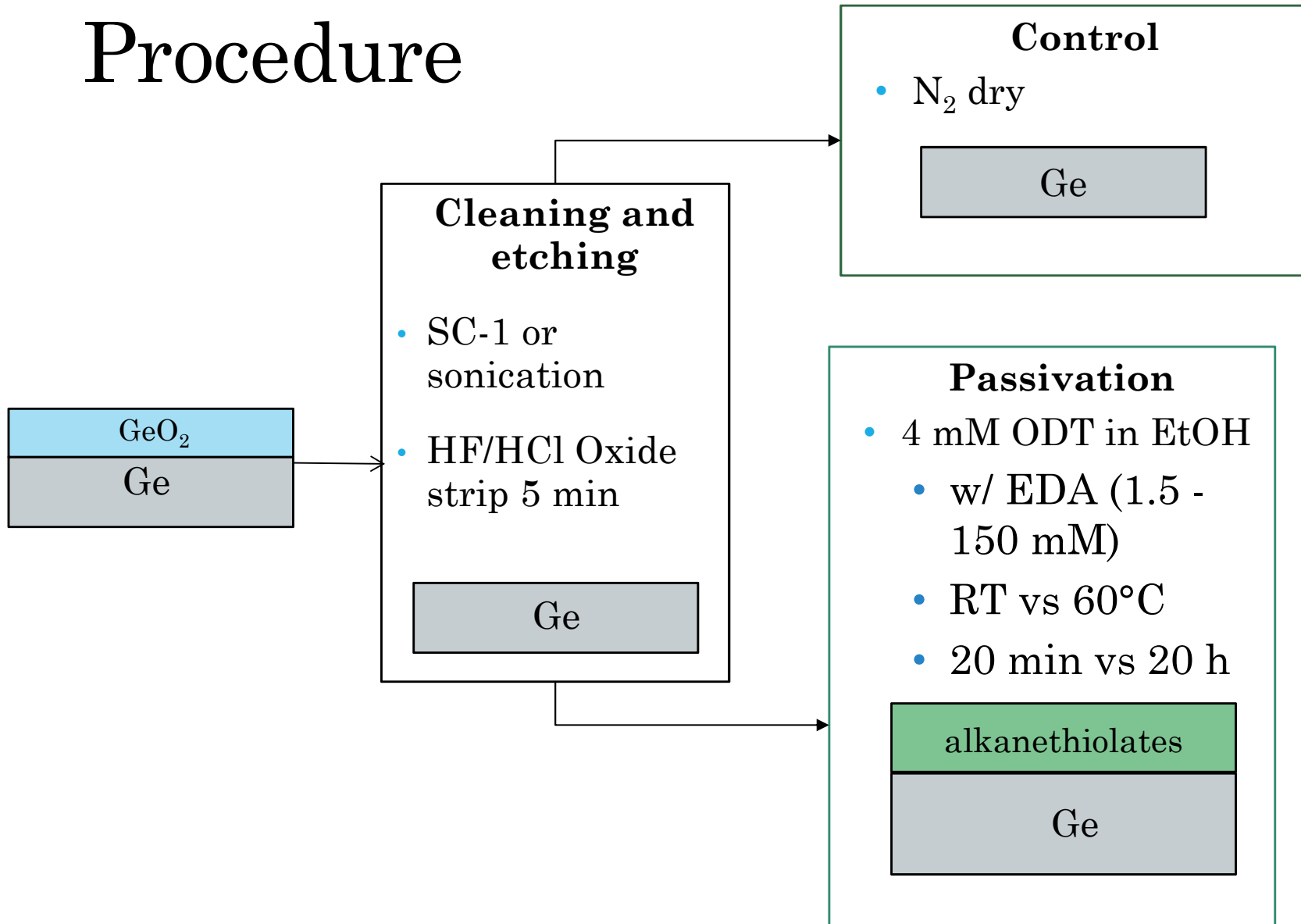


Objective

- **Goal:** Reduce the deposition time of a dense, highly-ordered alkanethiolate passivation.



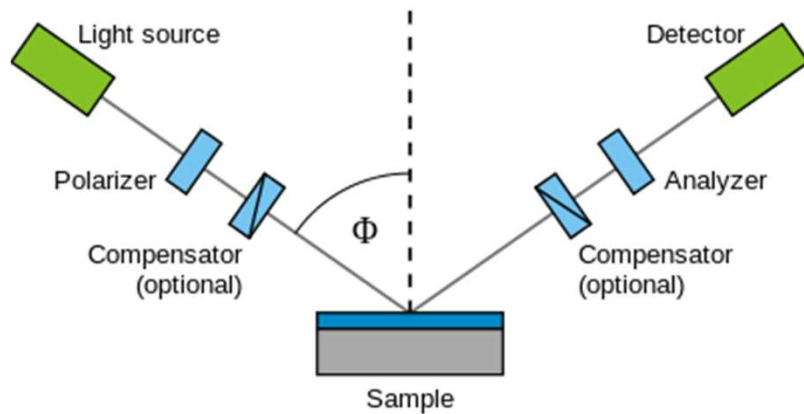
Procedure



Characterization

Spectroscopic ellipsometry

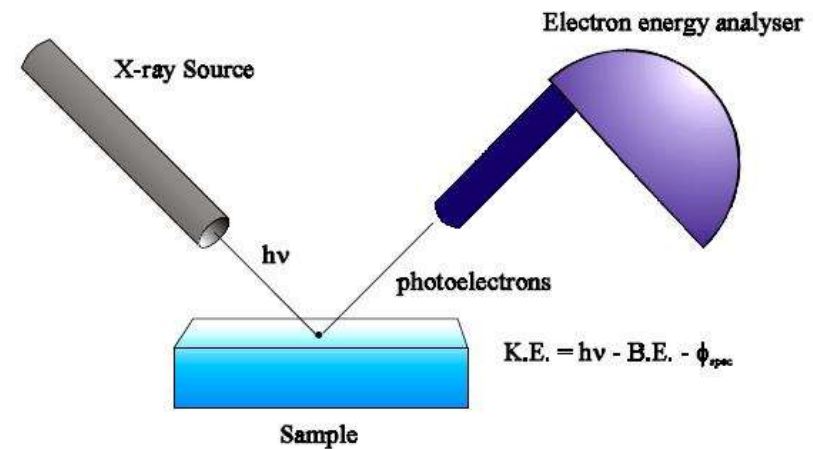
- Measured overlayer (oxides) thickness



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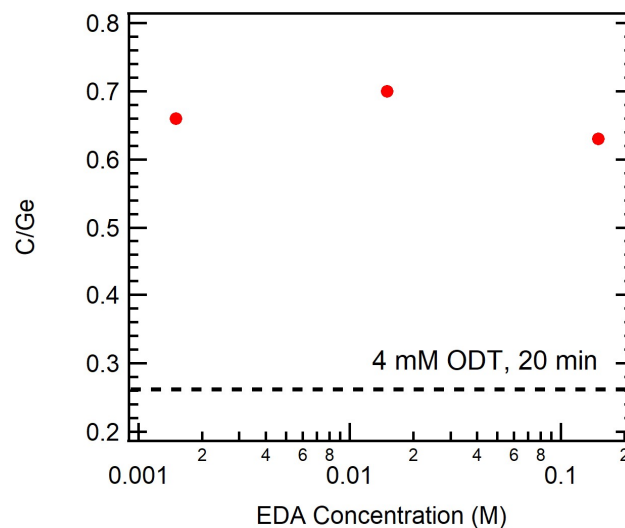
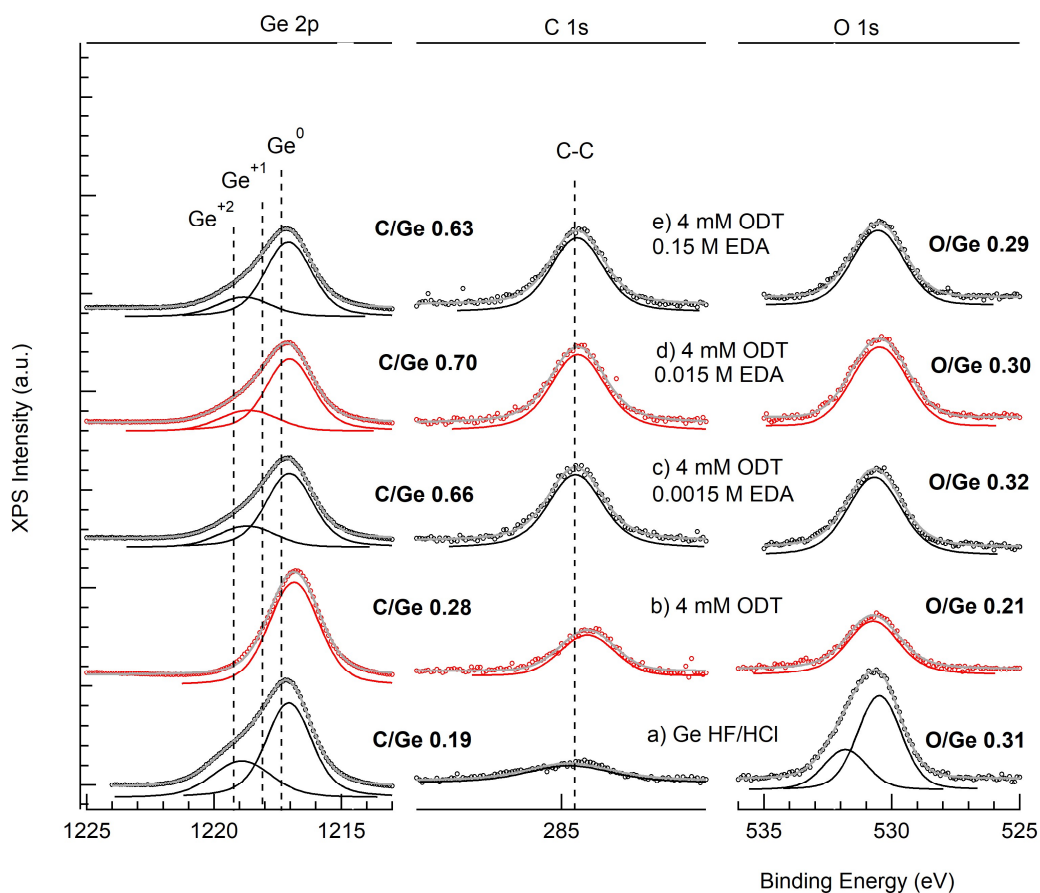
X-ray photoelectron spectroscopy (XPS)

- Determine chemical species on surface.



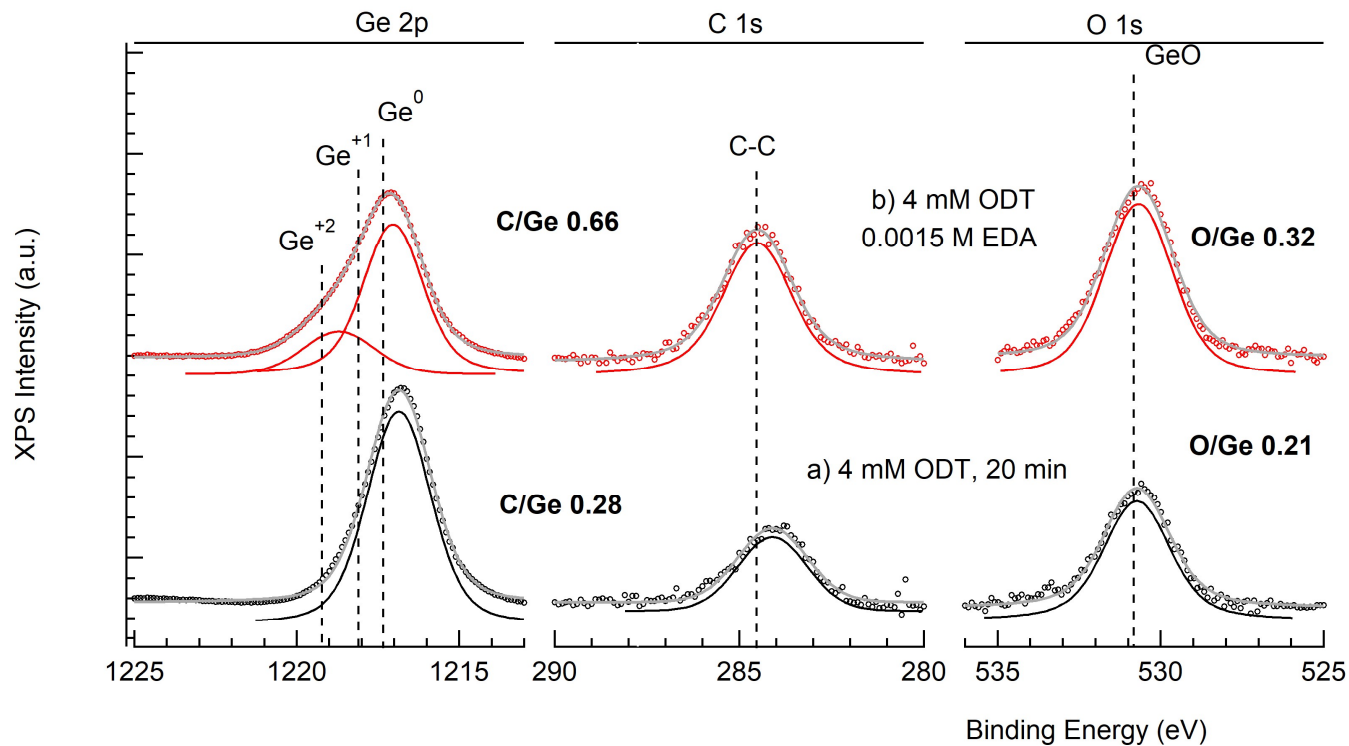
Wikipedia

Amine increases carbon coverage



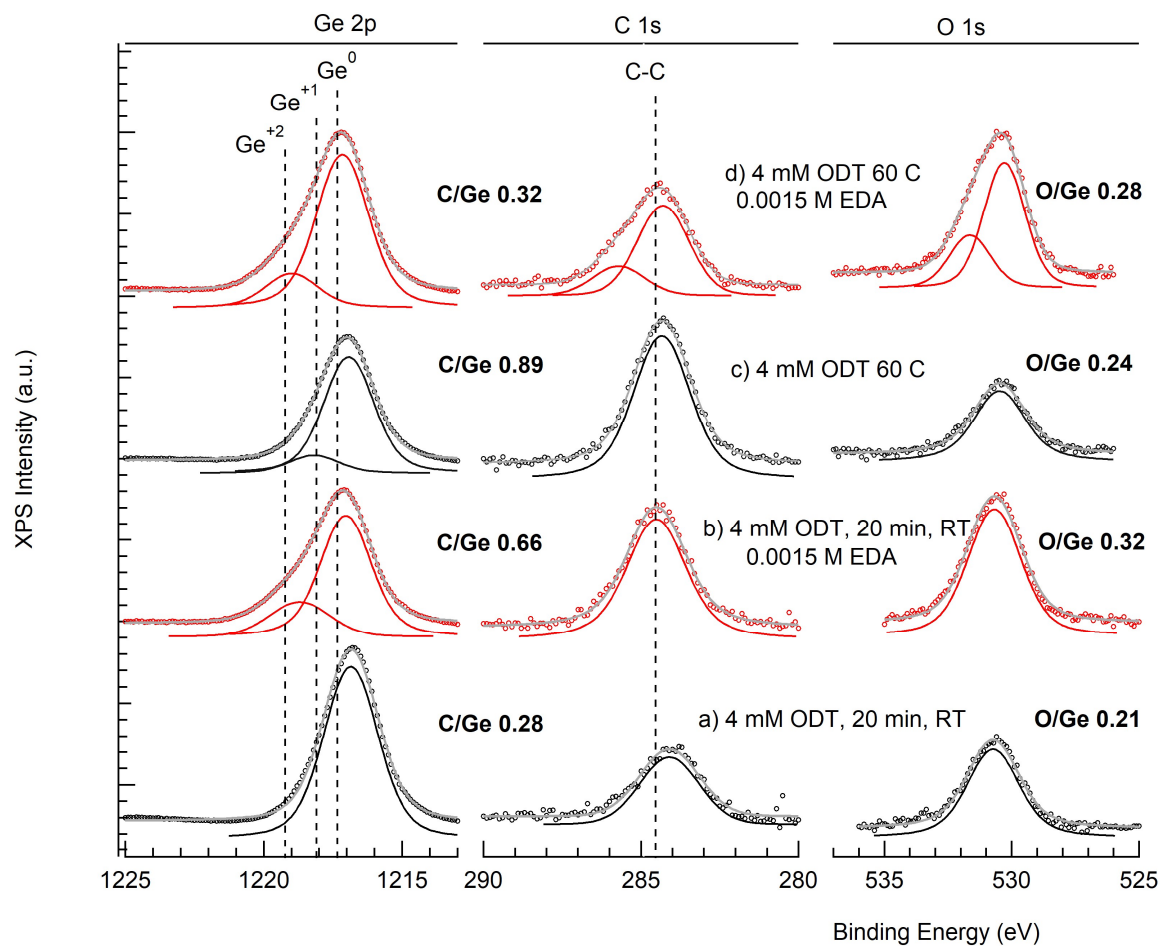
- Amine does not oxidize the surface.
- Concentration of amine does not affect coverage

For 20 h immersion, amine decreases C/Ge ratio



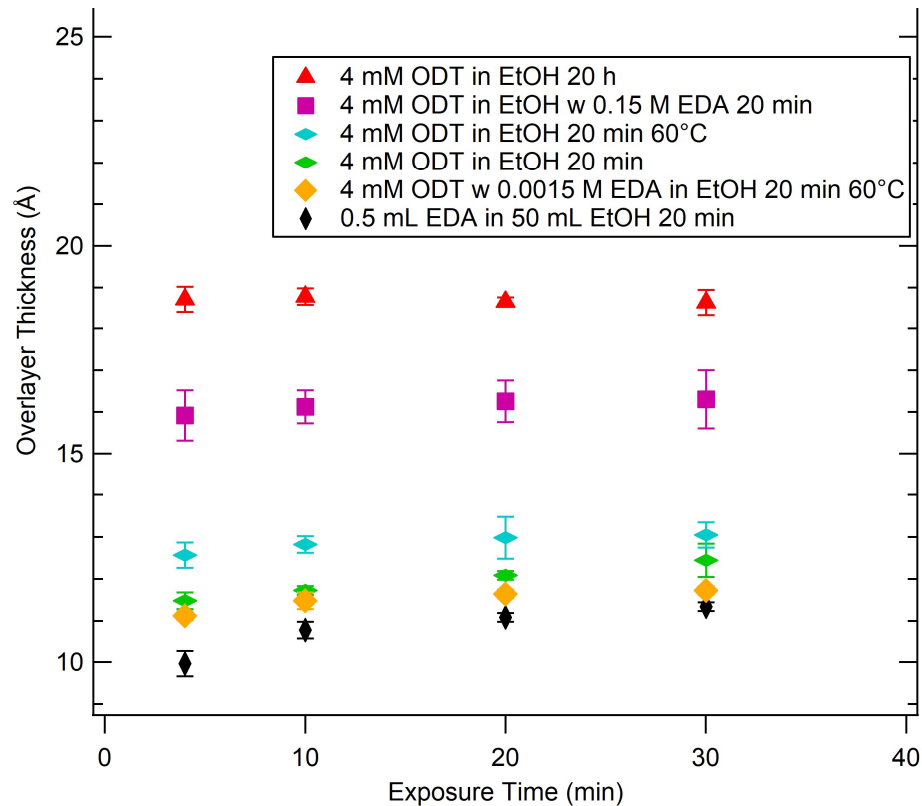
- At 20 h, thiol and amine solutions show a decrease in the C/Ge ratio than just thiol alone.

Increasing temperature with amine decreases C/Ge ratio



- Increasing temperature increase C/Ge ratio for thiol alone, but decreases C/Ge ratio for thiol and amine solutions.

Overlayer thickness corroborates XPS results



- With EDA, increasing T
→ Lower thickness
- At 60°C, adding EDA
→ Lower thickness
- At RT, adding EDA
→ higher thickness
- ODT alone, increasing T
→ higher thickness

Conclusions

- EDA helps at RT and does not contribute to oxidation.
- 20 h immersion produces a more dense and highly-ordered layer than 20 min immersion
- Increasing temperature for solutions with EDA does not produce a more dense and highly-ordered layer.

Future Work

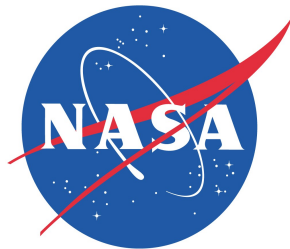
- Confirm temperature trends.

Acknowledgements

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Lam Research



Thank you!

